

Role of Si and C Impurities in Yellow and Blue Luminescence of Unintentionally and Si-Doped GaN

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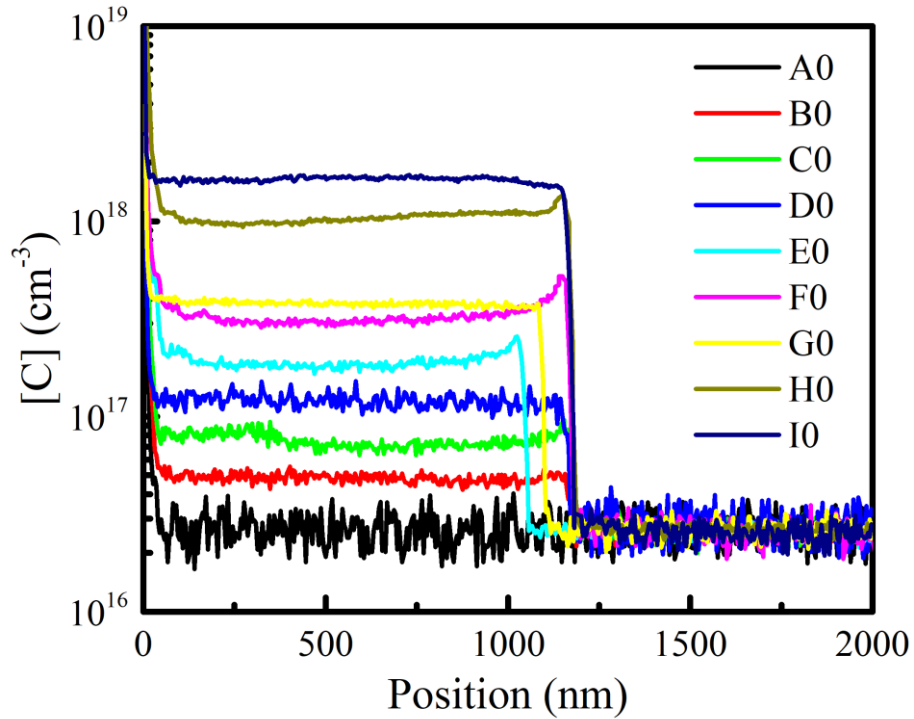


Figure S1. Secondary ion mass spectroscopy results of carbon impurity in samples A0–I0.

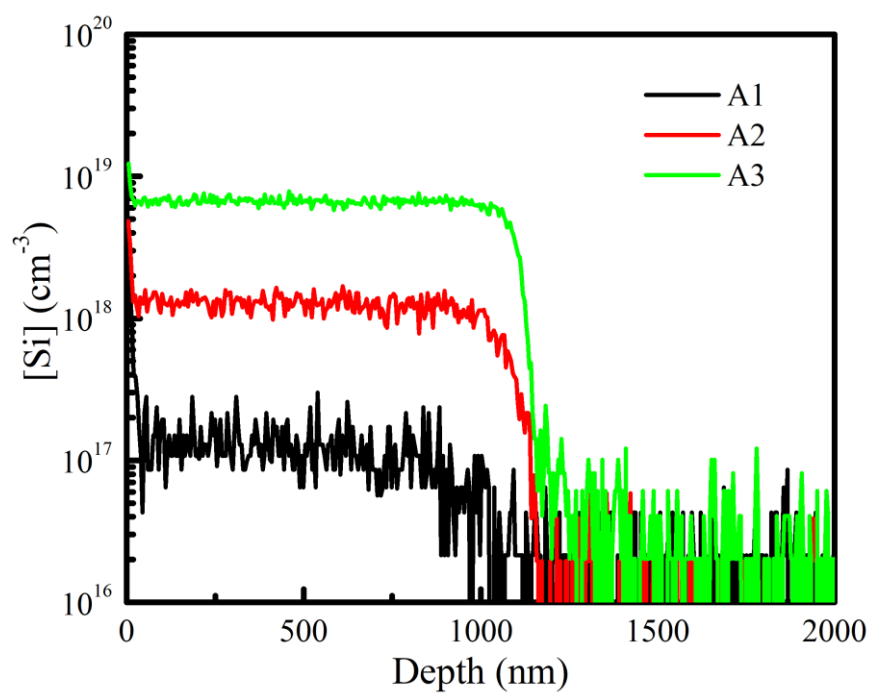


Figure S2. Secondary ion mass spectroscopy results of Si concentration in samples A1–A3.